Ãœmit Ã–zgÃ¼r

List of Publications by Year
in descending order

48 papers	2,620 citations	430874 18 h-index	265206 42 g-index
48 all docs	48 docs citations	48 times ranked	3599 citing authors

#	Article	IF	Citations
1	ZnO Devices and Applications: A Review of Current Status and Future Prospects. Proceedings of the IEEE, 2010, 98, 1255-1268.	21.3	669
2	Microwave ferrites, part 1: fundamental properties. Journal of Materials Science: Materials in Electronics, 2009, 20, 789-834.	2.2	348
3	On the efficiency droop in InGaN multiple quantum well blue light emitting diodes and its reduction with p-doped quantum well barriers. Applied Physics Letters, 2008, 93, .	3.3	301
4	Reduction of efficiency droop in InGaN light emitting diodes by coupled quantum wells. Applied Physics Letters, 2008, 93, .	3.3	208
5	Micro-LEDs, a Manufacturability Perspective. Applied Sciences (Switzerland), 2019, 9, 1206.	2.5	188
6	Microwave ferrites, part 2: passive components and electrical tuning. Journal of Materials Science: Materials in Electronics, 2009, 20, 911-952.	2.2	110
7	High electron mobility in nearly lattice-matched AlInNâˆ•AlNâˆ•GaN heterostructure field effect transistors. Applied Physics Letters, 2007, 91, 132116.	3.3	107
8	GaN-Based Light-Emitting Diodes: Efficiency at High Injection Levels. Proceedings of the IEEE, 2010, 98, 1180-1196.	21.3	103
9	Recent Development of Boron Nitride towards Electronic Applications. Advanced Electronic Materials, 2017, 3, 1600485.	5.1	98
10	Carrier dynamics in bulk GaN. Journal of Applied Physics, 2012, 111, .	2.5	65
11	Metalâ€“Semiconductor Hybrid Aerogels: Evolution of Optoelectronic Properties in a Low-Dimensional CdSe/Ag Nanoparticle Assembly. ACS Nano, 2015, 9, 9810-9821.	14.6	44
12	Status of Growth of Group III-Nitride Heterostructures for Deep Ultraviolet Light-Emitting Diodes. Crystals, 2017, 7, 300.	2.2	39
13	Ultra-small Ge1âˆ’xSnx quantum dots with visible photoluminescence. Chemical Communications, 2016, 52, 11665-11668.	4.1	30
14	Large pyroelectric effect in undoped epitaxial Pb(Zr,Ti)O3 thin films on SrTiO3 substrates. Applied Physics Letters, 2008, 93, 052913.	3.3	27
15	Ferromagnetism in ZnO- and GaN-Based Diluted Magnetic Semiconductors: Achievements and Challenges. Proceedings of the IEEE, 2010, 98, 1288-1301.	21.3	26
16	Energy Gap Tuning and Carrier Dynamics in Colloidal Ge_{1â€“x}Sn_x Quantum Dots. Journal of Physical Chemistry Letters, 2016, 7, 3295-3301.	4.6	23
17	Defect reduction in GaN epilayers grown by metal-organic chemical vapor deposition with in situ SiNx nanonetwork. Applied Physics Letters, 2007, 90, 262112.	3.3	21
18	Field-assisted emission in AlGaN/GaN heterostructure field-effect transistors using low-frequency noise technique. Journal of Applied Physics, 2011, 109, .	2.5	19

#	Article	IF	Citations
19	Polarity control and residual strain in ZnO epilayers grown by molecular beam epitaxy on (0001) GaN/sapphire. Physica Status Solidi - Rapid Research Letters, 2016, 10, 682-686.	2.4	19
20	Large electro-optic effect in single-crystal Pb(Zr,Ti)O3 (001) measured by spectroscopic ellipsometry. Journal of Applied Physics, 2008, 104, 093103.	2.5	18
21	Epitaxial growth of (001)-oriented Ba0.5Sr0.5TiO3 thin films on a-plane sapphire with an MgO/ZnO bridge layer. Applied Physics Letters, 2009, 95, 212901.	3.3	17
22	Effect of large strain on dielectric and ferroelectric properties of Ba0.5Sr0.5TiO3 thin films. Applied Physics Letters, 2009, 95, 012907.	3.3	15
23	Enhanced microwave dielectric tunability of Ba0.5Sr0.5TiO3 thin films grown with reduced strain on DyScO3 substrates by three-step technique. Journal of Applied Physics, 2013, 113, 044108.	2.5	13
24	Plasmonic titanium nitride via atomic layer deposition: A low-temperature route. Journal of Applied Physics, 2020, 127, .	2.5	12
25	Facile synthesis of highly luminescent lithium silicate nanocrystals with varying crystal structures and morphology. CrystEngComm, 2019, 21, 1974-1983.	2.6	11
26	Thickness Variations and Absence of Lateral Compositional Fluctuations in Aberration-Corrected STEM Images of InGaN LED Active Regions at Low Dose. Microscopy and Microanalysis, 2014, 20, 864-868.	0.4	10
27	Highâ€Performance BeMgZnO/ZnO Heterostructure Fieldâ€Effect Transistors. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000371.	2.4	10
28	Characterization of Ag Schottky Barriers on Be_{0.02}Mg_{0.26}ZnO/ZnO Heterostructures. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1700366.	2.4	9
29	A Platform for Complementary Metalâ€Oxideâ€Semiconductor Compatible Plasmonics: High Plasmonic Quality Titanium Nitride Thin Films on Si (001) with a MgO Interlayer. Advanced Photonics Research, 2021, 2, 2000210.	3.6	8
30	Measurements of generationâ€recombination effect by lowâ€frequency phaseâ€noise technique in AlGaN/GaN MOSHFETs. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1539-1543.	0.8	6
31	Influence of ZnO thin film crystallinity on in vitro biocompatibility. Toxicology Research, 2018, 7, 754-759.	2.1	6
32	Polarity Control within One Monolayer at ZnO/GaN Heterointerface: (0001) Plane Inversion Domain Boundary. ACS Applied Materials & Interfaces, 2018, 10, 37651-37660.	8.0	5
33	Solution-Processed Ge_{1â€“x} Sn_x Alloy Nanocrystal Thin Films with High Electrical Conductivity and Tunable Energy Gaps. Chemistry of Materials, 2021, 33, 6897-6908.	6.7	5
34	Structural and Optical Properties of PbTiO3 Grown on SrTiO3 Substrates by Peroxide MBE. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	4
35	Reduction of Flicker Noise in AlGaN/GaN-Based HFETs After High Electric-Field Stress. IEEE Electron Device Letters, 2011, 32, 1513-1515.	3.9	4
36	Carrier dynamics under two- and single-photon excitation in bulk GaN. Physica Status Solidi (B): Basic Research, 2012, 249, 503-506.	1.5	4

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37	Highâ€Quality Plasmonic Materials TiN and ZnO:Al by Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100227.	2.4	4
38	Comparative study of BeMgZnO/ZnO heterostructures on c-sapphire and GaN by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	3
39	Growth of High-Quality Pb(ZrxTi1-x)O3 Films by Peroxide MBE and Their Optical and Structural Characteristics. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	2
40	Stress test measurements of lattice-matched InAlN/AlN/GaN HFET structures. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1345-1347.	1.8	2
41	Hot-electron noise spectroscopy for HFET channels. , 2017, , .		2
42	Energy-Efficient, On-Demand Activation of Biosensor Arrays for Long-Term Continuous Health Monitoring. Biosensors, 2022, 12, 358.	4.7	2
43	The effect of barrier strain on the reliability of In_x Al_{1â€“x}N/AlN/GaN heterostructure fieldâ€effect transistors. Physica Status Solidi - Rapid Research Letters, 2012, 6, 163-165.	2.4	1
44	Electron energy relaxation in wurtzite ZnO and GaN. , 2013, , .		1
45	Fabrication of Schottky Diodes on Zn-polar BeMgZnO/ZnO Heterostructure Grown by Plasma-assisted Molecular Beam Epitaxy. Journal of Visualized Experiments, 2018, , .	0.3	1
46	Persistent Photoconductivity in High-mobility AlxGa1â^'xN/AlN/GaN Heterostructures Grown by Metal-organic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
47	Photoelectrochemical Etching of GaN Thin Films With Varying Carrier Concentrations. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
48	Design and Optimization of an Acoustic Metamaterial Lens. , 2020, , .		0